Docket No: 242604US2SRDDIV

Inventor: KOJI ASAKAWA ET AL

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Amendment to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the

application:

Listing of Claims:

Claims 1-20 (Canceled)

Claim 21 (New) A mask used for exposing a porous substrate to form a first region

and a second region, said first region being filled with a conductive material piercing through

the entire thickness of the porous substrate to constitute an interfacial conductive portion, said

second region being filled with a conductive material not piercing the entire thickness of the

porous substrate to constitute a non-interfacial conductive portion, said mask comprising:

a first light-transmitting region for exposing said first region, and

a second light-transmitting region for exposing said second region,

said second light-transmitting region including an aggregation of fine patterns of

which an average aperture ratio is not more than 50% of an average aperture ratio of said first

light-transmitting region and

a size of said fine patterns of said second light-transmitting region being in a range

of $0.1\mu m$ to $10\mu m$.

Claim 22. (New) The mask according to claim 21, wherein said fine patterns of said

second light-transmitting region are circular or polygonal in configuration, and said fine

patterns are arranged in a triangular lattice pattern.

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Claim 23. (New) The mask according to claim 22, wherein said fine patterns of said second light-transmitting region are circular in configuration, and a center-to-center distance between the neighboring circles is at least twice as large as the diameter of said circle.

Claim 24. (New) The mask according to claim 21, wherein said fine patterns of said second light-transmitting region are circular or polygonal in configuration, and said fine patterns are arranged to form a square lattice.

Claim 25. (New) The mask according to Claim 21, wherein said fine patterns are stripe patterns having aperture ratio of not more than 50%, and a width between the neighboring stripe patterns is in a range of $0.1 \mu m$ to $10 \mu m$.